

IN THE CLAIMS:

Please amend claim 4 and add new claims 14-19 as follows:

4. (Amended) A semiconductor device comprising:

a substrate;

a source/drain diffused layer formed in the substrate for a transistor; and

a dummy diffused layer formed in the substrate;

wherein the source/drain diffused layer has its surface silicided, and

wherein the dummy diffused layer has its surface covered with a dummy gate electrode at least partially.

14. (New) The device of claim 1, wherein the dummy diffused layer is located between a circuit block and another circuit block.

15. (New) The device of claim 1, wherein the dummy diffused layer is not electrically coupled to another component via an interconnect.

16. (New) The device of claim 4, wherein the dummy diffused layer is located between a circuit block and another circuit block.

17. (New) The device of claim 4, wherein the dummy diffused layer is not electrically coupled to another component via an interconnect.

18. (New) A method of making a semiconductor device comprising: